

isc Silicon NPN Power Transistor

2SC3729

DESCRIPTION

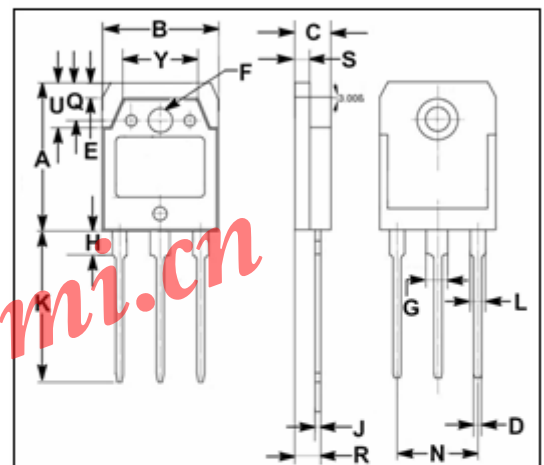
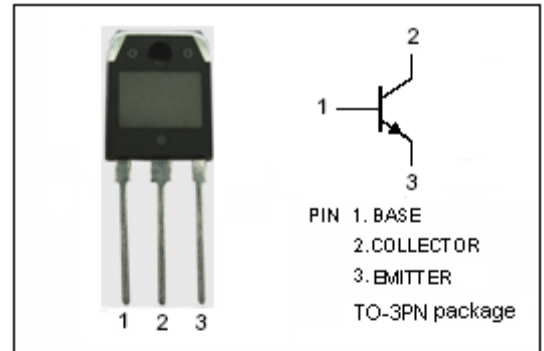
- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 800V(\text{Min})$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base voltage	6	V
$I_C$	Collector Current-Continuous	5	A
$I_{CM}$	Collector Current-Peak	16	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

**isc Silicon NPN Power Transistor****2SC3729****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown voltage	$I_E=10\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1.25\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1.25\text{A}$			1.5	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1500\text{V}; R_{BE}=0$			0.5	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$			8	

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